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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	26
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2.5K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	36-WFLGA
Supplier Device Package	36-WFLGA (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104caala-u0

○ ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/G14			
			30 pins	32 pins	36 pins	40 pins
192 KB	8 KB	20 KB	—	—	—	R5F104EH
128 KB	8 KB	16 KB	R5F104AG	R5F104BG	R5F104CG	R5F104EG
96 KB	8 KB	12 KB	R5F104AF	R5F104BF	R5F104CF	R5F104EF
64 KB	4 KB	5.5 KB Note	R5F104AE	R5F104BE	R5F104CE	R5F104EE
48 KB	4 KB	5.5 KB Note	R5F104AD	R5F104BD	R5F104CD	R5F104ED
32 KB	4 KB	4 KB	R5F104AC	R5F104BC	R5F104CC	R5F104EC
16 KB	4 KB	2.5 KB	R5F104AA	R5F104BA	R5F104CA	R5F104EA

Flash ROM	Data flash	RAM	RL78/G14			
			44 pins	48 pins	52 pins	64 pins
512 KB	8 KB	48 KB Note	—	R5F104GL	—	R5F104LL
384 KB	8 KB	32 KB	—	R5F104GK	—	R5F104LK
256 KB	8 KB	24 KB Note	R5F104FJ	R5F104GJ	R5F104JJ	R5F104LJ
192 KB	8 KB	20 KB	R5F104FH	R5F104GH	R5F104JH	R5F104LH
128 KB	8 KB	16 KB	R5F104FG	R5F104GG	R5F104JG	R5F104LG
96 KB	8 KB	12 KB	R5F104FF	R5F104GF	R5F104JF	R5F104LF
64 KB	4 KB	5.5 KB Note	R5F104FE	R5F104GE	R5F104JE	R5F104LE
48 KB	4 KB	5.5 KB Note	R5F104FD	R5F104GD	R5F104JD	R5F104LD
32 KB	4 KB	4 KB	R5F104FC	R5F104GC	R5F104JC	R5F104LC
16 KB	4 KB	2.5 KB	R5F104FA	R5F104GA	—	—

Flash ROM	Data flash	RAM	RL78/G14	
			80 pins	100 pins
512 KB	8 KB	48 KB Note	R5F104ML	R5F104PL
384 KB	8 KB	32 KB	R5F104MK	R5F104PK
256 KB	8 KB	24 KB Note	R5F104MJ	R5F104PJ
192 KB	8 KB	20 KB	R5F104MH	R5F104PH
128 KB	8 KB	16 KB	R5F104MG	R5F104PG
96 KB	8 KB	12 KB	R5F104MF	R5F104PF

The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F104xD (x = A to C, E to G, J, L): Start address FE900H

R5F104xE (x = A to C, E to G, J, L): Start address FE900H

R5F104xJ (x = F, G, J, L, M, P): Start address F9F00H

R5F104xL (x = G, L, M, P): Start address F3F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

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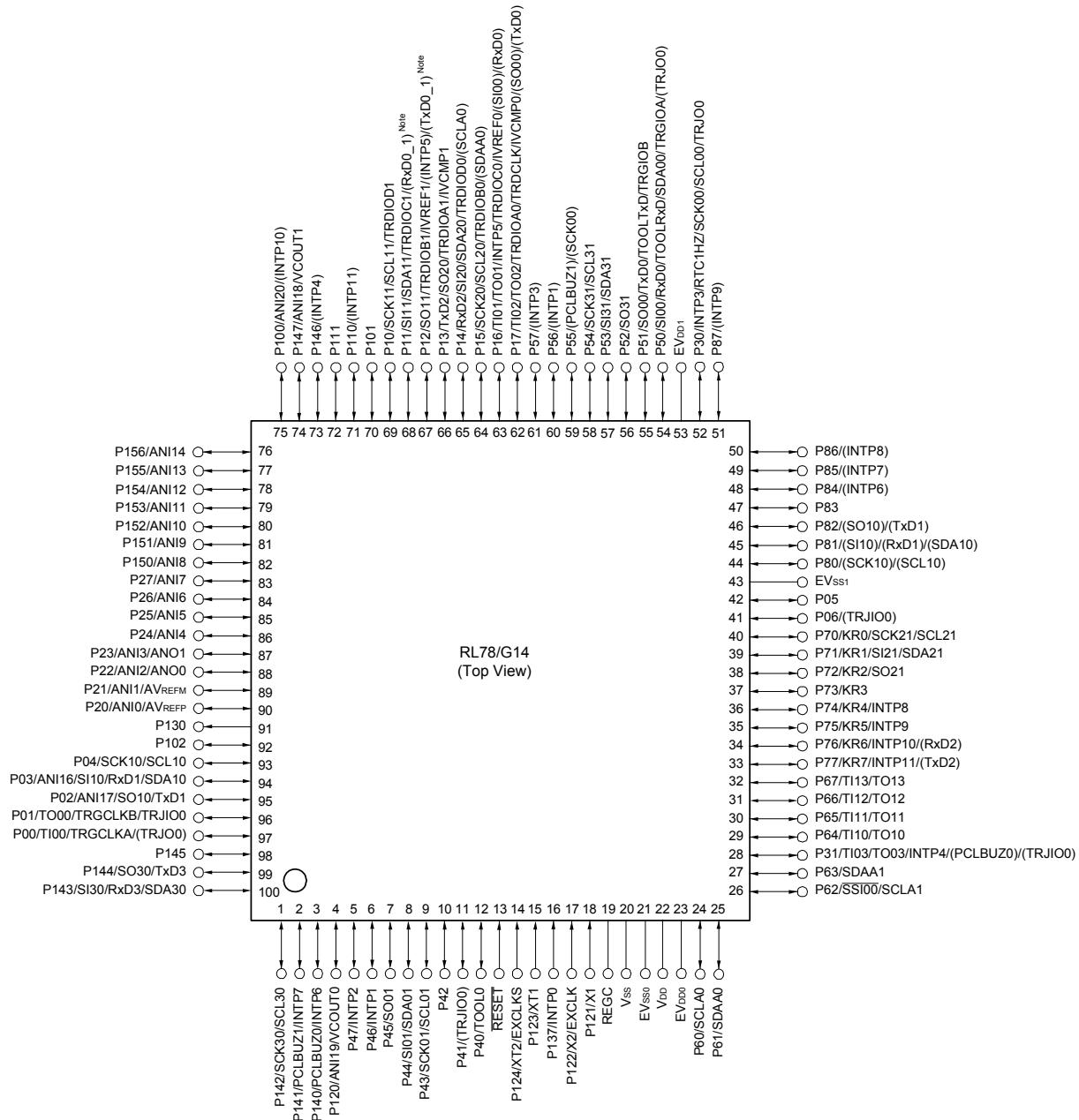
Pin count	Package	Fields of Application Note	Ordering Part Number
40 pins	40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)	A	R5F104EAANA#U0, R5F104ECANA#U0, R5F104EDANA#U0, R5F104EEANA#U0, R5F104EFANA#U0, R5F104EGANA#U0, R5F104EHANA#U0 R5F104EAANA#W0, R5F104ECANA#W0, R5F104EDANA#W0, R5F104EEANA#W0, R5F104EFANA#W0, R5F104EGANA#W0, R5F104EHANA#W0
		D	R5F104EADNA#U0, R5F104ECDNA#U0, R5F104EDDNA#U0, R5F104EEDNA#U0, R5F104EFDNA#U0, R5F104EGDNA#U0, R5F104EHDNA#U0 R5F104EADNA#W0, R5F104ECDNA#W0, R5F104EDDNA#W0, R5F104EEDNA#W0, R5F104EFDNA#W0, R5F104EGDNA#W0, R5F104EHDNA#W0
		G	R5F104EAGNA#U0, R5F104ECGNA#U0, R5F104EDGNA#U0, R5F104EEGNA#U0, R5F104EFGNA#U0, R5F104EGGNA#U0, R5F104EHGNA#U0 R5F104EAGNA#W0, R5F104ECGNA#W0, R5F104EDGNA#W0, R5F104EEGNA#W0, R5F104EFGNA#W0, R5F104EGGNA#W0, R5F104EHGNA#W0
44 pins	44-pin plastic LQFP (10 × 10, 0.8 mm pitch)	A	R5F104FAAFP#V0, R5F104FC AFP#V0, R5F104FDAFP#V0, R5F104FEA FP#V0, R5F104FFA FP#V0, R5F104FG AFP#V0, R5F104FH AFP#V0, R5F104FJA FP#V0 R5F104FAAFP#X0, R5F104FC AFP#X0, R5F104FDAFP#X0, R5F104FEA FP#X0, R5F104FFA FP#X0, R5F104FG AFP#X0, R5F104FH AFP#X0, R5F104FJA FP#X0
		D	R5F104FADFP#V0, R5F104FCDFP#V0, R5F104FDDFP#V0, R5F104FEDFP#V0, R5F104FFDFP#V0, R5F104FGDFP#V0, R5F104FHDFP#V0, R5F104FJD FP#V0 R5F104FADFP#X0, R5F104FCDFP#X0, R5F104FDDFP#X0, R5F104FEDFP#X0, R5F104FFDFP#X0, R5F104FGDFP#X0, R5F104FHDFP#X0, R5F104FJD FP#X0
		G	R5F104FAGFP#V0, R5F104FC GFP#V0, R5F104FD GFP#V0, R5F104FEGFP#V0, R5F104FF GFP#V0, R5F104FG GFP#V0, R5F104FH GFP#V0, R5F104FJ GFP#V0 R5F104FAGFP#X0, R5F104FC GFP#X0, R5F104FD GFP#X0, R5F104FEGFP#X0, R5F104FF GFP#X0, R5F104FG GFP#X0, R5F104FH GFP#X0, R5F104FJ GFP#X0

Note For the fields of application, refer to **Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.10 100-pin products

- 100-pin plastic LFQFP (14 × 14 mm, 0.5 mm pitch)



Note Mounted on the 384 KB or more code flash memory products.

Caution 1. Make EVss0, EVss1 pins the same potential as Vss pin.

Caution 2. Make VDD pin the potential that is higher than EVDD0, EVDD1 pins (EVDD0 = EVDD1).

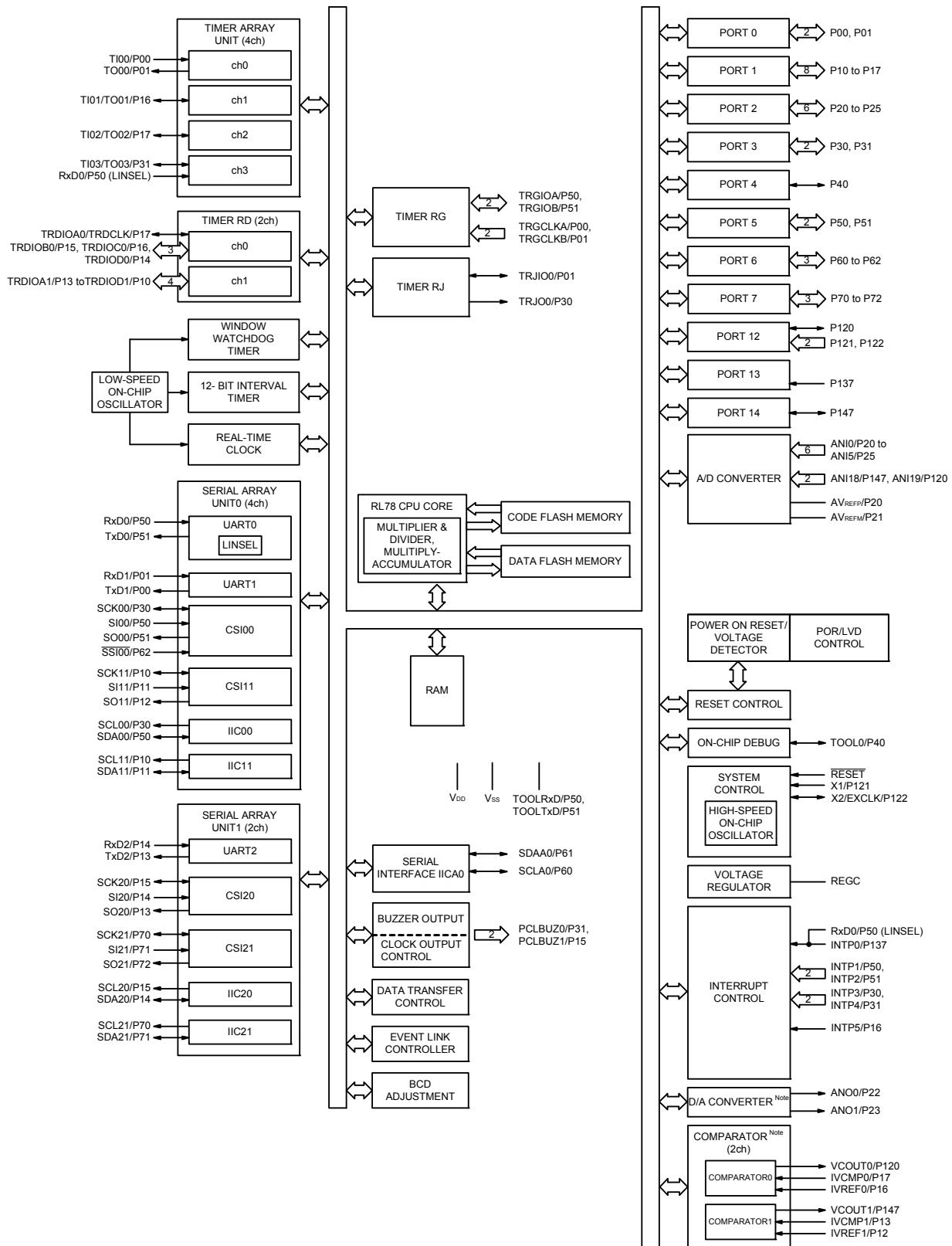
Caution 3. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see [1.4 Pin Identification](#).

Remark 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{VDD0} and EV_{VDD1} pins and connect the V_{SS}, EV_{VSS0} and EV_{VSS1} pins to separate ground lines.

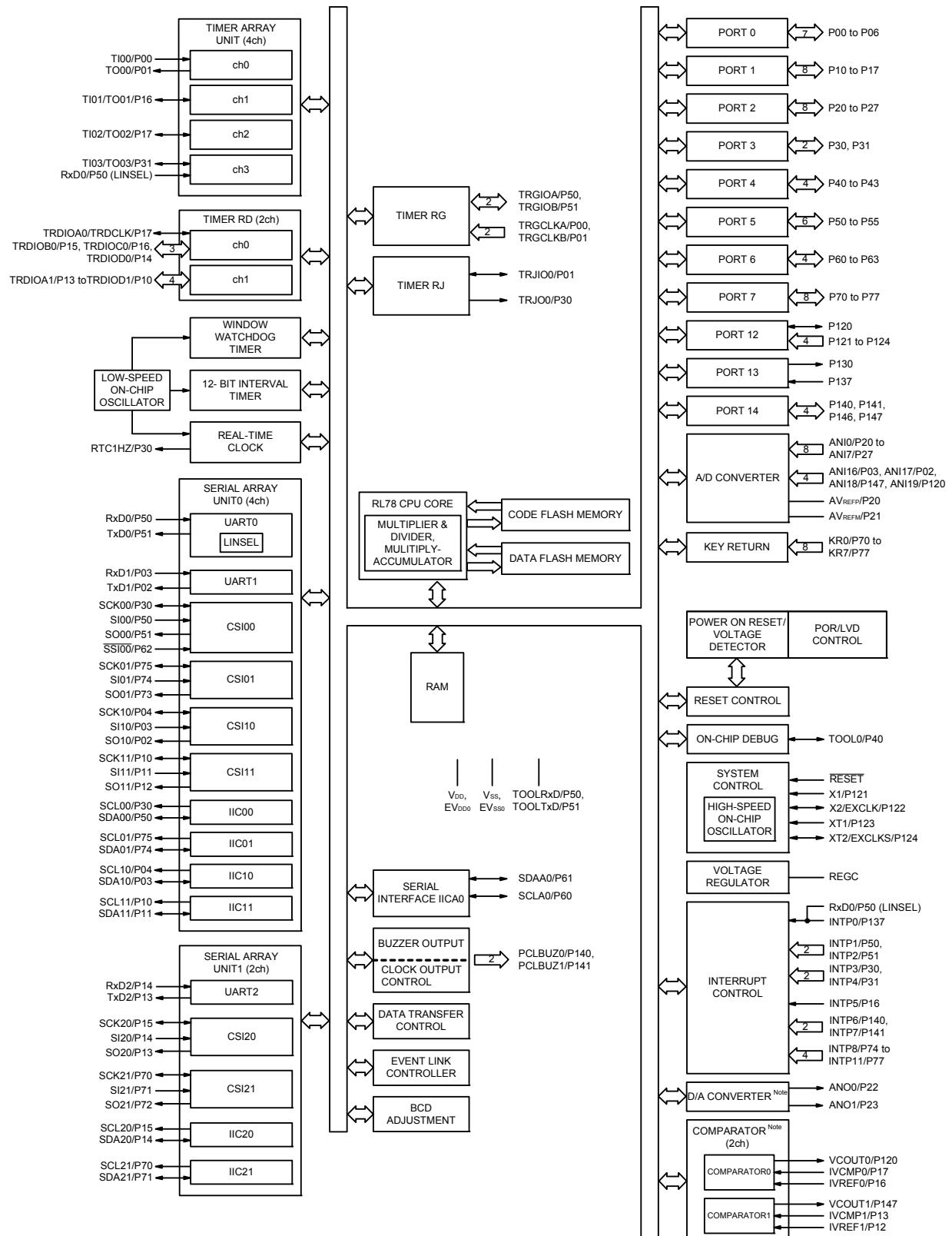
Remark 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

1.5.3 36-pin products



Note Mounted on the 96 KB or more code flash memory products.

1.5.8 64-pin products



Note Mounted on the 96 KB or more code flash memory products.

[30-pin, 32-pin, 36-pin, 40-pin products (code flash memory 96 KB to 256 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

Item	30-pin	32-pin	36-pin	40-pin
	R5F104Ax (x = F, G)	R5F104Bx (x = F, G)	R5F104Cx (x = F, G)	R5F104Ex (x = F to H)
Code flash memory (KB)	96 to 128	96 to 128	96 to 128	96 to 192
Data flash memory (KB)	8	8	8	8
RAM (KB)	12 to 16 Note	12 to 16 Note	12 to 16 Note	12 to 20 Note
Address space	1 MB			
Main system clock	High-speed system clock X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)			
	High-speed on-chip oscillator clock (f_{IH}) HS (high-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)			
Subsystem clock		—		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz
Low-speed on-chip oscillator clock	15 kHz (TYP.): V_{DD} = 1.6 to 5.5 V			
General-purpose register	8 bits × 32 registers (8 bits × 8 registers × 4 banks)			
Minimum instruction execution time	0.03125 µs (High-speed on-chip oscillator clock: f_{IH} = 32 MHz operation) 0.05 µs (High-speed system clock: f_{MX} = 20 MHz operation) — 30.5 µs (Subsystem clock: f_{SUB} = 32.768 kHz operation)			
Instruction set	<ul style="list-style-type: none"> • Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 			
I/O port	Total	26	28	32
	CMOS I/O	21	22	26
	CMOS input	3	3	3
	CMOS output	—	—	—
	N-ch open-drain I/O (6 V tolerance)	2	3	3
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)		
	Watchdog timer	1 channel		
	Real-time clock (RTC)	1 channel		
	12-bit interval timer	1 channel		
	Timer output	Timer outputs: 13 channels PWM outputs: 9 channels		
	RTC output	—		1 • 1 Hz (subsystem clock: f_{SUB} = 32.768 kHz)

(Note is listed on the next page.)

[44-pin, 48-pin, 52-pin, 64-pin products (code flash memory 96 KB to 256 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

Item	44-pin	48-pin	52-pin	64-pin	
	R5F104Fx (x = F to H, J)	R5F104Gx (x = F to H, J)	R5F104Jx (x = F to H, J)	R5F104Lx (x = F to H, J)	
Code flash memory (KB)	96 to 256	96 to 256	96 to 256	96 to 256	
Data flash memory (KB)	8	8	8	8	
RAM (KB)	12 to 24 Note	12 to 24 Note	12 to 24 Note	12 to 24 Note	
Address space	1 MB				
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)			
	High-speed on-chip oscillator clock (f_{IH})	HS (high-speed main) mode: 1 to 32 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)			
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz			
Low-speed on-chip oscillator clock		15 kHz (TYP.): $V_{DD} = 1.6$ to 5.5 V			
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)			
Minimum instruction execution time		0.03125 µs (High-speed on-chip oscillator clock: $f_{IH} = 32$ MHz operation) 0.05 µs (High-speed system clock: $f_{MX} = 20$ MHz operation) 30.5 µs (Subsystem clock: $f_{SUB} = 32.768$ kHz operation)			
Instruction set		<ul style="list-style-type: none"> • Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 			
I/O port	Total	40	44	48	58
	CMOS I/O	31	34	38	48
	CMOS input	5	5	5	5
	CMOS output	—	1	1	1
	N-ch open-drain I/O (6 V tolerance)	4	4	4	4
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)			
	Watchdog timer	1 channel			
	Real-time clock (RTC)	1 channel			
	12-bit interval timer	1 channel			
	Timer output	Timer outputs: 14 channels PWM outputs: 9 channels			
	RTC output	1 • 1 Hz (subsystem clock: $f_{SUB} = 32.768$ kHz)			

(Note is listed on the next page.)

2.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

(TA = -40 to +85°C, 1.6 V ≤ EV_{D0} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{S0} = 0 V)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	IDD1	Operating mode	HS (high-speed main mode Note 5	f _{HOCO} = 64 MHz, f _{IH} = 32 MHz Note 3	Basic operation	V _{DD} = 5.0 V		2.4		mA
						V _{DD} = 3.0 V		2.4		
		HS (high-speed main mode Note 5	f _{HOCO} = 32 MHz, f _{IH} = 32 MHz Note 3	Basic operation	V _{DD} = 5.0 V		2.1			mA
						V _{DD} = 3.0 V		2.1		
			f _{HOCO} = 64 MHz, f _{IH} = 32 MHz Note 3	Normal operation	V _{DD} = 5.0 V		5.1	8.7		
						V _{DD} = 3.0 V		5.1	8.7	
			f _{HOCO} = 32 MHz, f _{IH} = 32 MHz Note 3	Normal operation	V _{DD} = 5.0 V		4.8	8.1		
						V _{DD} = 3.0 V		4.8	8.1	
			f _{HOCO} = 48 MHz, f _{IH} = 24 MHz Note 3	Normal operation	V _{DD} = 5.0 V		4.0	6.9		
						V _{DD} = 3.0 V		4.0	6.9	
		f _{HOCO} = 24 MHz, f _{IH} = 24 MHz Note 3	Normal operation	V _{DD} = 5.0 V			3.8	6.3		
					V _{DD} = 3.0 V		3.8	6.3		
			f _{HOCO} = 16 MHz, f _{IH} = 16 MHz Note 3	Normal operation	V _{DD} = 5.0 V		2.8	4.6		
						V _{DD} = 3.0 V		2.8	4.6	
		LS (low-speed main mode Note 5	f _{HOCO} = 8 MHz, f _{IH} = 8 MHz Note 3	Normal operation	V _{DD} = 3.0 V		1.3	2.0		mA
						V _{DD} = 2.0 V		1.3	2.0	
		LV (low-voltage main mode Note 5	f _{HOCO} = 4 MHz, f _{IH} = 4 MHz Note 3	Normal operation	V _{DD} = 3.0 V		1.3	1.8		mA
						V _{DD} = 2.0 V		1.3	1.8	
		HS (high-speed main mode Note 5	f _{MX} = 20 MHz Note 2, V _{DD} = 5.0 V	Normal operation	Square wave input		3.3	5.3		mA
					Resonator connection		3.4	5.5		
			f _{MX} = 20 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		3.3	5.3		
					Resonator connection		3.4	5.5		
			f _{MX} = 10 MHz Note 2, V _{DD} = 5.0 V	Normal operation	Square wave input		2.0	3.1		
					Resonator connection		2.1	3.2		
			f _{MX} = 10 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		2.0	3.1		
					Resonator connection		2.1	3.2		
		LS (low-speed main mode Note 5	f _{MX} = 8 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		1.2	1.9		mA
					Resonator connection		1.2	2.0		
			f _{MX} = 8 MHz Note 2, V _{DD} = 2.0 V	Normal operation	Square wave input		1.2	1.9		
					Resonator connection		1.2	2.0		
		Subsystem clock operation	f _{SUB} = 32.768 kHz Note 4 TA = -40°C	Normal operation	Square wave input		4.7	6.1		μA
					Resonator connection		4.7	6.1		
			f _{SUB} = 32.768 kHz Note 4 TA = +25°C	Normal operation	Square wave input		4.7	6.1		
					Resonator connection		4.7	6.1		
			f _{SUB} = 32.768 kHz Note 4 TA = +50°C	Normal operation	Square wave input		4.8	6.7		
					Resonator connection		4.8	6.7		
			f _{SUB} = 32.768 kHz Note 4 TA = +70°C	Normal operation	Square wave input		4.8	7.5		
					Resonator connection		4.8	7.5		
			f _{SUB} = 32.768 kHz Note 4 TA = +85°C	Normal operation	Square wave input		5.4	8.9		
					Resonator connection		5.4	8.9		

(Notes and Remarks are listed on the next page.)

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, Vss = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	IDD1	Operating mode	HS (high-speed main) mode Note 5	fHO CO = 64 MHz, fIH = 32 MHz Note 3	Basic operation	VDD = 5.0 V		2.6	
						VDD = 3.0 V		2.6	
				fHO CO = 32 MHz, fIH = 32 MHz Note 3	Basic operation	VDD = 5.0 V		2.3	
						VDD = 3.0 V		2.3	
		HS (high-speed main) mode Note 5	fHO CO = 64 MHz, fIH = 32 MHz Note 3	Normal operation	VDD = 5.0 V		5.4	10.2	mA
						VDD = 3.0 V		5.4	10.2
			fHO CO = 32 MHz, fIH = 32 MHz Note 3	Normal operation	VDD = 5.0 V		5.0	9.6	
						VDD = 3.0 V		5.0	9.6
			fHO CO = 48 MHz, fIH = 24 MHz Note 3	Normal operation	VDD = 5.0 V		4.2	7.8	
						VDD = 3.0 V		4.2	7.8
		LS (low-speed main) mode Note 5	fHO CO = 24 MHz, fIH = 24 MHz Note 3	Normal operation	VDD = 5.0 V		4.0	7.4	
						VDD = 3.0 V		4.0	7.4
			fHO CO = 16 MHz, fIH = 16 MHz Note 3	Normal operation	VDD = 5.0 V		3.0	5.3	
						VDD = 3.0 V		3.0	5.3
		LV (low-voltage main) mode Note 5	fHO CO = 8 MHz, fIH = 8 MHz Note 3	Normal operation	VDD = 3.0 V		1.4	2.3	mA
						VDD = 2.0 V		1.4	2.3
		HS (high-speed main) mode Note 5	fHO CO = 4 MHz, fIH = 4 MHz Note 3	Normal operation	VDD = 3.0 V		1.3	1.9	mA
						VDD = 2.0 V		1.3	1.9
			fMX = 20 MHz Note 2, VDD = 5.0 V	Normal operation	Square wave input		3.4	6.2	mA
					Resonator connection		3.6	6.4	
			fMX = 20 MHz Note 2, VDD = 3.0 V	Normal operation	Square wave input		3.4	6.2	
					Resonator connection		3.6	6.4	
		LS (low-speed main) mode Note 5	fMX = 10 MHz Note 2, VDD = 5.0 V	Normal operation	Square wave input		2.1	3.6	mA
					Resonator connection		2.2	3.7	
			fMX = 10 MHz Note 2, VDD = 3.0 V	Normal operation	Square wave input		2.1	3.6	
					Resonator connection		2.2	3.7	
		Subsystem clock operation	fMX = 8 MHz Note 2, VDD = 3.0 V	Normal operation	Square wave input		1.2	2.2	mA
					Resonator connection		1.2	2.3	
			fMX = 8 MHz Note 2, VDD = 2.0 V	Normal operation	Square wave input		1.2	2.2	
					Resonator connection		1.2	2.3	
			fSUB = 32.768 kHz Note 4 TA = -40°C	Normal operation	Square wave input		4.9	7.1	μA
					Resonator connection		4.9	7.1	
			fSUB = 32.768 kHz Note 4 TA = +25°C	Normal operation	Square wave input		4.9	7.1	
					Resonator connection		4.9	7.1	
			fSUB = 32.768 kHz Note 4 TA = +50°C	Normal operation	Square wave input		5.1	8.8	
					Resonator connection		5.1	8.8	
			fSUB = 32.768 kHz Note 4 TA = +70°C	Normal operation	Square wave input		5.5	10.5	
					Resonator connection		5.5	10.5	
			fSUB = 32.768 kHz Note 4 TA = +85°C	Normal operation	Square wave input		6.5	14.5	
					Resonator connection		6.5	14.5	

(Notes and Remarks are listed on the next page.)

(3) Flash ROM: 384 to 512 KB of 48- to 100-pin products

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, Vss = EVSS0 = EVSS1 = 0 V)

(2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	IDD2 Note 2	HALT mode HS (high-speed main) mode Note 7	fHO CO = 64 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.93	3.32		mA
				VDD = 3.0 V		0.93	3.32		
			fHO CO = 32 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.5	2.63		
				VDD = 3.0 V		0.5	2.63		
			fHO CO = 48 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.72	2.60		
				VDD = 3.0 V		0.72	2.60		
			fHO CO = 24 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.42	2.03		
				VDD = 3.0 V		0.42	2.03		
			fHO CO = 16 MHz, fIH = 16 MHz Note 4	VDD = 5.0 V		0.39	1.50		
				VDD = 3.0 V		0.39	1.50		
		LS (low-speed main) mode Note 7	fHO CO = 8 MHz, fIH = 8 MHz Note 4	VDD = 3.0 V		270	800		μA
				VDD = 2.0 V		270	800		
		LV (low-voltage main) mode Note 7	fHO CO = 4 MHz, fIH = 4 MHz Note 4	VDD = 3.0 V		450	755		μA
				VDD = 2.0 V		450	755		
		HS (high-speed main) mode Note 7	fMX = 20 MHz Note 3, VDD = 5.0 V	Square wave input		0.31	1.69		mA
				Resonator connection		0.41	1.91		
			fMX = 20 MHz Note 3, VDD = 3.0 V	Square wave input		0.31	1.69		
				Resonator connection		0.41	1.91		
			fMX = 10 MHz Note 3, VDD = 5.0 V	Square wave input		0.21	0.94		
				Resonator connection		0.26	1.02		
			fMX = 10 MHz Note 3, VDD = 3.0 V	Square wave input		0.21	0.94		
				Resonator connection		0.26	1.02		
			fMX = 8 MHz Note 3, VDD = 3.0 V	Square wave input		110	610		μA
				Resonator connection		150	660		
		LS (low-speed main) mode Note 7	fMX = 8 MHz Note 3, VDD = 2.0 V	Square wave input		110	610		
				Resonator connection		150	660		
		Subsystem clock operation	fsUB = 32.768 kHz Note 5, TA = -40°C	Square wave input		0.31			μA
				Resonator connection		0.50			
			fsUB = 32.768 kHz Note 5, TA = +25°C	Square wave input		0.38	0.76		
				Resonator connection		0.57	0.95		
			fsUB = 32.768 kHz Note 5, TA = +50°C	Square wave input		0.47	3.59		
				Resonator connection		0.70	3.78		
			fsUB = 32.768 kHz Note 5, TA = +70°C	Square wave input		0.80	6.20		
				Resonator connection		1.00	6.39		
			fsUB = 32.768 kHz Note 5, TA = +85°C	Square wave input		1.65	10.56		
				Resonator connection		1.84	10.75		
		STOP mode Note 8	TA = -40°C			0.19			μA
			TA = +25°C			0.30	0.59		
			TA = +50°C			0.41	3.42		
			TA = +70°C			0.80	6.03		
			TA = +85°C			1.53	10.39		

(Notes and Remarks are listed on the next page.)

- Note 5.** Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and I_{WDT} when the watchdog timer is in operation.
- Note 6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and I_{AADC} when the A/D converter operates in an operation mode or the HALT mode.
- Note 7.** Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and I_{LVD} when the LVD circuit is in operation.
- Note 8.** Current flowing during programming of the data flash.
- Note 9.** Current flowing during self-programming.
- Note 10.** For shift time to the SNOOZE mode, see **23.3.3 SNOOZE mode** in the RL78/G14 User's Manual.
- Note 11.** Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and I_{DAC} when the D/A converter operates in an operation mode or the HALT mode.
- Note 12.** Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2, or IDD3 and I_{CMP} when the comparator circuit is in operation.
- Note 13.** A comparator and D/A converter are provided in products with 96 KB or more code flash memory.

Remark 1. f_{IL}: Low-speed on-chip oscillator clock frequency

Remark 2. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 3. f_{CLK}: CPU/peripheral hardware clock frequency

Remark 4. Temperature condition of the TYP. value is TA = 25°C

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, Vss = EVSS0 = EVSS1 = 0 V) (2/2)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Timer RD input high-level width, low-level width	tTDIH, tTDIL	TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIODC0, TRDIODC1, TRDIOD0, TRDIOD1		3/fCLK			ns
Timer RD forced cutoff signal input low-level width	tTDSIL	P130/INTP0	2MHz < fCLK ≤ 32 MHz	1			μs
			fCLK ≤ 2 MHz	1/fCLK + 1			
Timer RG input high-level width, low-level width	tTRGIH, tTGIL	TRGIOA, TRGIOB		2.5/fCLK			ns
TO00 to TO03, TO10 to TO13, TRJIO0, TRJOO, TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIODC0, TRDIODC1, TRDIOD0, TRDIOD1, TRGIOA, TRGIOB output frequency	fro	HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
			2.7 V ≤ EVDD0 < 4.0 V			8	MHz
			1.8 V ≤ EVDD0 < 2.7 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
		LS (low-speed main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
		LV (low-voltage main) mode	1.6 V ≤ EVDD0 ≤ 5.5 V			2	MHz
		HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
			2.7 V ≤ EVDD0 < 4.0 V			8	MHz
			1.8 V ≤ EVDD0 < 2.7 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
PCLBUZ0, PCLBUZ1 output frequency	fPCL	LS (low-speed main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
		LV (low-voltage main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
			1.6 V ≤ EVDD0 ≤ 5.5 V			4	MHz
Interrupt input high-level width, low-level width	tINTH, tINTL	INTP0	1.6 V ≤ VDD ≤ 5.5 V	1			μs
		INTP1 to INTP11	1.6 V ≤ EVDD0 ≤ 5.5 V	1			μs
Key interrupt input low-level width	tKR	KR0 to KR7	1.8 V ≤ EVDD0 ≤ 5.5 V	250			ns
			1.6 V ≤ EVDD0 < 1.8 V	1			μs
RESET low-level width	tRSL			10			μs

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)(TA = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCL _r clock frequency	f _{SCL}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 50 pF, R _b = 2.7 kΩ		1000 Note 1		300 Note 1		300 Note 1	kHz
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ		1000 Note 1		300 Note 1		300 Note 1	kHz
		4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ		400 Note 1		300 Note 1		300 Note 1	kHz
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ		400 Note 1		300 Note 1		300 Note 1	kHz
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V Note 2, C _b = 100 pF, R _b = 5.5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCL _r = "L"	t _{LOW}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 50 pF, R _b = 2.7 kΩ	475		1550		1550		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ	475		1550		1550		ns
		4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	1150		1550		1550		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	1150		1550		1550		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V Note 2, C _b = 100 pF, R _b = 5.5 kΩ	1550		1550		1550		ns
Hold time when SCL _r = "H"	t _{HIGH}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 50 pF, R _b = 2.7 kΩ	245		610		610		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ	200		610		610		ns
		4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	675		610		610		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	600		610		610		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V Note 2, C _b = 100 pF, R _b = 5.5 kΩ	610		610		610		ns

- Note 1.** Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{VSS0}, and EV_{VSS1}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2.** During HALT instruction execution by flash memory.
- Note 3.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4.** When high-speed system clock and subsystem clock are stopped.
- Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6.** Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V @ 1 MHz to 32 MHz
2.4 V ≤ V_{DD} ≤ 5.5 V @ 1 MHz to 16 MHz
- Note 8.** Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (64 MHz max.)

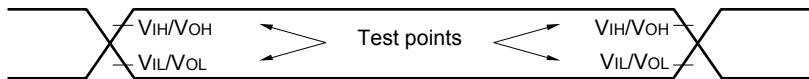
Remark 3. f_{IH}: High-speed on-chip oscillator clock frequency (32 MHz max.)

Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ 5.5 V, V_{SS} = EV_{VSS0} = EV_{VSS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate Note 1		2.4 V ≤ EV _{DD0} ≤ 5.5 V Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} Note 3		f _{MCK} /12 Note 2	bps
				2.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

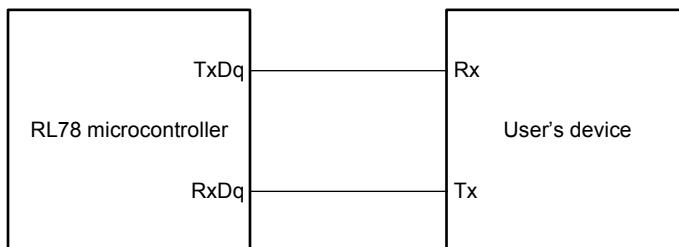
However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. The following conditions are required for low voltage interface when EV_{DD0} < V_{DD}.
2.4 V ≤ EV_{DD0} < 2.7 V: MAX. 1.3 Mbps

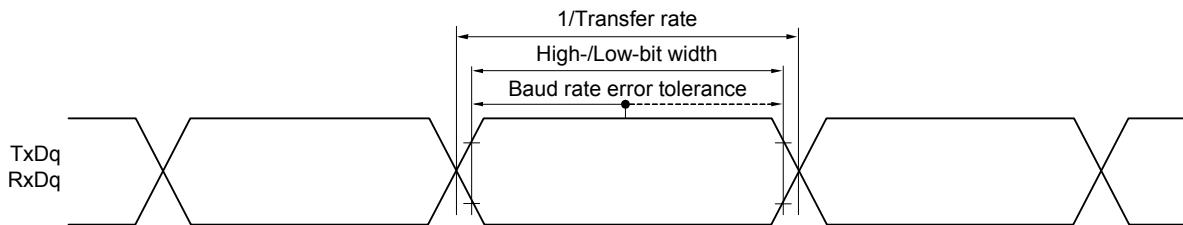
Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
HS (high-speed main) mode: 32 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

Remark 2. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{VSS0} = EV_{VSS1} = 0 V) (2/3)

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
Slp setup time (to SCKp↑) ^{Note}	tsIK1	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	162		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	354		ns
		2.4 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	958		ns
Slp hold time (from SCKp↑) ^{Note}	tKSI1	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	38		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	38		ns
		2.4 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	38		ns
Delay time from SCKp↓ to SOp output ^{Note}	tKS01	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ		200	ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ		390	ns
		2.4 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{VSS0} = EV_{VSS1} = 0 V) (3/3)

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
Slp setup time (to SCKp _↓) ^{Note}	tsIK1	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	88		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	88		ns
		2.4 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	220		ns
Slp hold time (from SCKp _↓) ^{Note}	tKSI1	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	38		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	38		ns
		2.4 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	38		ns
Delay time from SCKp _↑ to SO _p output ^{Note}	tKS01	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ		50	ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ		50	ns
		2.4 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ		50	ns

Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SO_p pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

- (4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 to ANI14, ANI16 to ANI20

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, 1.6 V ≤ EVDD = EVDD1 ≤ VDD, VSS = EVSS0 = EVSS1 = 0 V,

Reference voltage (+) = VBGR Note 3, Reference voltage (-) = AVREFM = 0 V Note 4, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit	
Conversion time	tCONV	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	Ezs	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±0.60	% FSR
Integral linearity error Note 1	ILE	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±1.0	LSB
Analog input voltage	VAIN			0		VBGR Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

Note 4. When reference voltage (-) = Vss, the MAX. values are as follows.

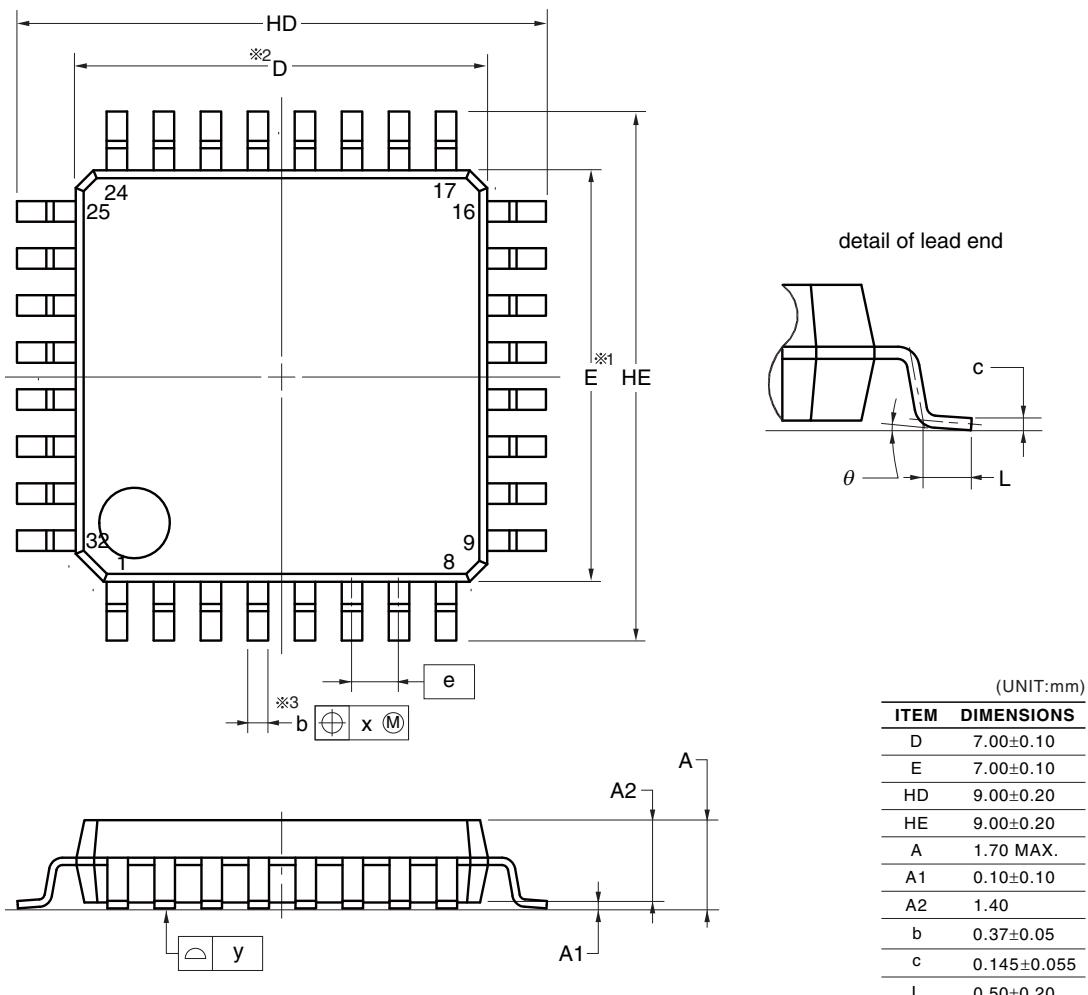
Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.

Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.

Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

R5F104BAAFP, R5F104BCA AFP, R5F104BDAFP, R5F104BEA FP, R5F104BFAFP, R5F104BG AFP
 R5F104BADFP, R5F104BCDFP, R5F104BDDFP, R5F104BEDFP, R5F104BFDFP, R5F104BGDFP
 R5F104BAGFP, R5F104BCGFP, R5F104BDGFP, R5F104BEGFP, R5F104BFGFP, R5F104BGGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP32-7x7-0.80	PLQP0032GB-A	P32GA-80-GBT-1	0.2

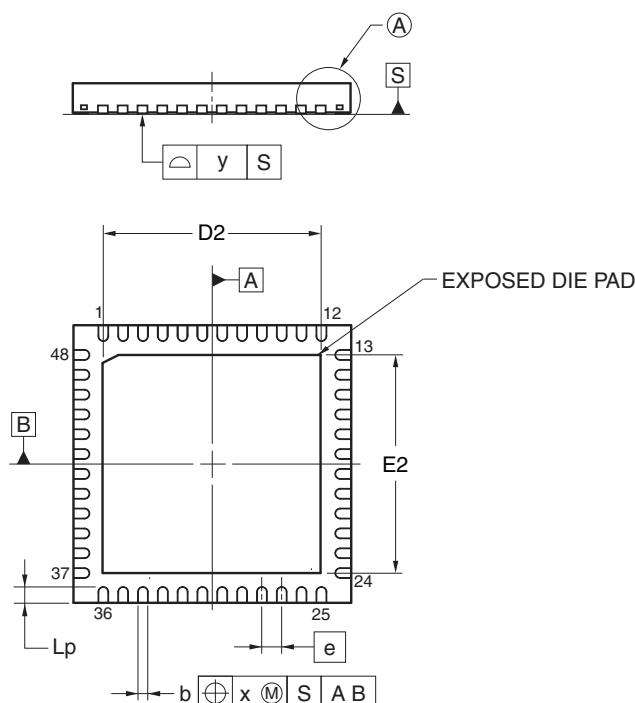
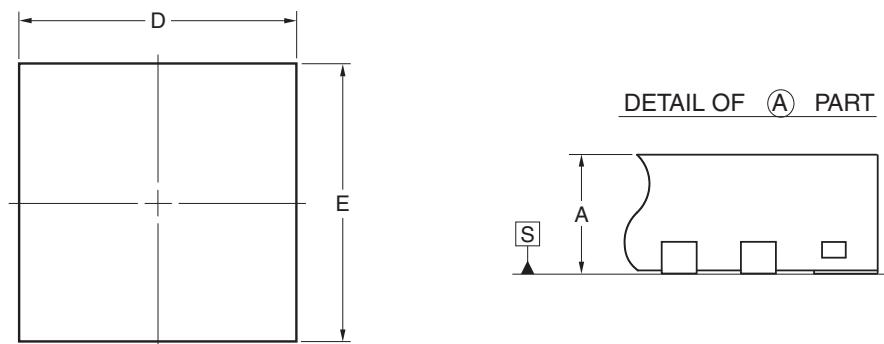
**NOTE**

- Dimensions “*1” and “*2” do not include mold flash.
- Dimension “*3” does not include trim offset.

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R5F104GAANA, R5F104GCANA, R5F104GDANA, R5F104GEANA, R5F104GFANA, R5F104GGANA,
 R5F104GHANA, R5F104GJANA
 R5F104GADNA, R5F104GCDNA, R5F104GDDNA, R5F104GEDNA, R5F104GFDNA, R5F104GGDNA,
 R5F104GHDNA, R5F104GJDNA
 R5F104GAGNA, R5F104GCGNA, R5F104GDGNA, R5F104GEGNA, R5F104GFGNA, R5F104GGGNA,
 R5F104GHGNA, R5F104GJGNA
 R5F104GKANA, R5F104GLANA
 R5F104GKGNA, R5F104GLGNA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN48-7x7-0.50	PWQN0048KB-A	48PQN-A P48K8-50-5B4-5	0.13



Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.95	7.00	7.05
E	6.95	7.00	7.05
A	0.70	0.75	0.80
b	0.18	0.25	0.30
[e]	—	0.50	—
Lp	0.30	0.40	0.50
x	—	—	0.05
y	—	—	0.05

ITEM	D2			E2			
	MIN	NOM	MAX	MIN	NOM	MAX	
EXPOSED DIE PAD VARIATIONS	A	5.45	5.50	5.55	5.45	5.50	5.55

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